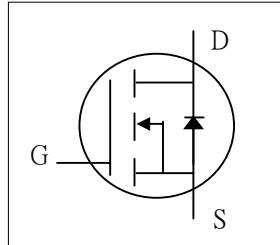


- ▼ 100% R_g & UIS Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free

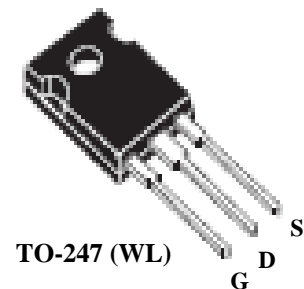


BV _{DSS}	600V
R _{DS(ON)}	95mΩ
I _D ^{3,6}	34A

Description

XP60BM095 series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-247 package is widely preferred for commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.



Absolute Maximum Ratings @T_j=25°C (unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	600	V
V _{GS}	Gate-Source Voltage	±20	V
V _{GS}	Gate-Source Voltage, AC (f > 1Hz)	±30	V
I _D @T _C =25°C	Drain Current, V _{GS} @ 10V ^{3,6}	34	A
I _D @T _C =100°C	Drain Current, V _{GS} @ 10V ^{3,6}	21.7	A
I _{DM}	Pulsed Drain Current ¹	80	A
dv/dt	MOSFET dv/dt Ruggedness (V _{DS} = 0 ...480V)	15	V/ns
P _D @T _C =25°C	Total Power Dissipation	208.3	W
P _D @T _A =25°C	Total Power Dissipation	3.12	W
E _{AS}	Single Pulse Avalanche Energy ⁴	200	mJ
dv/dt	Peak Diode Recovery dv/dt ⁵	30	V/ns
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
R _{thj-c}	Maximum Thermal Resistance, Junction-case	0.6	°C/W
R _{thj-a}	Maximum Thermal Resistance, Junction-ambient	40	°C/W

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	600	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =10A	-	-	95	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =10A	-	27	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =480V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±1	uA
Q _g	Total Gate Charge ⁷	I _D =10A	-	71	114	nC
Q _{gs}	Gate-Source Charge ⁷	V _{DS} =480V	-	16.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge ⁷	V _{GS} =10V	-	24	-	nC
t _{d(on)}	Turn-on Delay Time ⁷	V _{DD} =300V	-	30	-	ns
t _r	Rise Time ⁷	I _D =10A	-	33	-	ns
t _{d(off)}	Turn-off Delay Time ⁷	R _G =10Ω	-	150	-	ns
t _f	Fall Time ⁷	V _{GS} =10V	-	37	-	ns
C _{iss}	Input Capacitance ⁷	V _{GS} =0V	-	3080	4928	pF
C _{oss}	Output Capacitance ⁷	V _{DS} =400V	-	80	-	pF
C _{rss}	Reverse Transfer Capacitance ⁷	f=1.0MHz	-	10	-	pF
R _g	Gate Resistance	f=1.0MHz	-	6.5	13	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =10A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time ⁷	I _S =10A, V _{GS} =0V	-	290	-	ns
Q _{rr}	Reverse Recovery Charge ⁷	di/dt=100A/μs	-	4.3	-	uC

Notes:

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test
- 3.Ensure that the junction temperature does not exceed T_{Jmax}.
- 4.Starting T_j=25°C , V_{DD}=90V , L=100mH , R_G=25Ω , V_{GS}=10V , I_{AS}=2A
- 5.I_{SD} ≤ I_D, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C
- 6.Limited by max. junction temperature. Maximum duty cycle D=0.75
- 7.Guaranteed by design.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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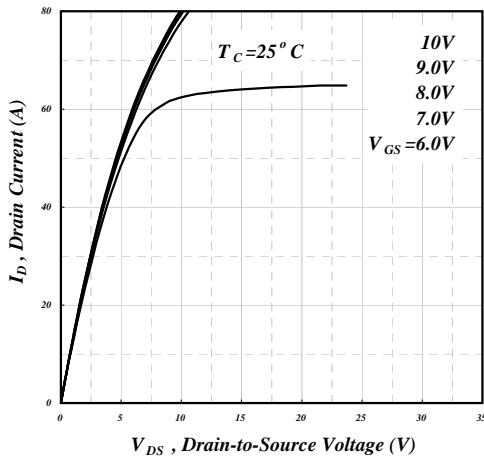


Fig 1. Typical Output Characteristics

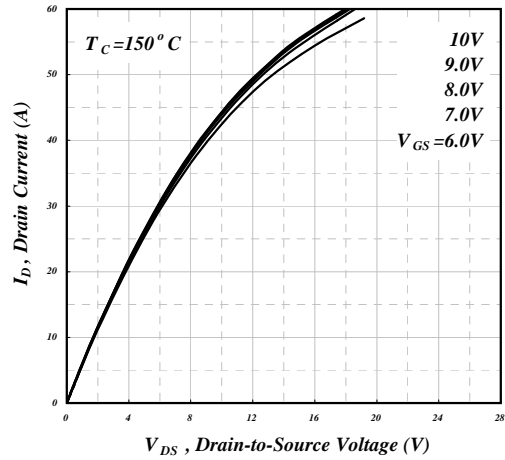


Fig 2. Typical Output Characteristics

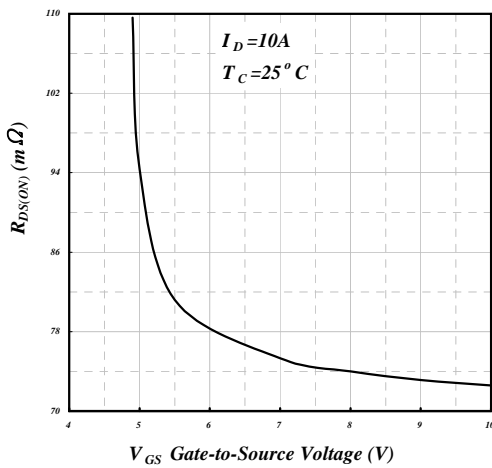


Fig 3. On-Resistance v.s. Gate Voltage

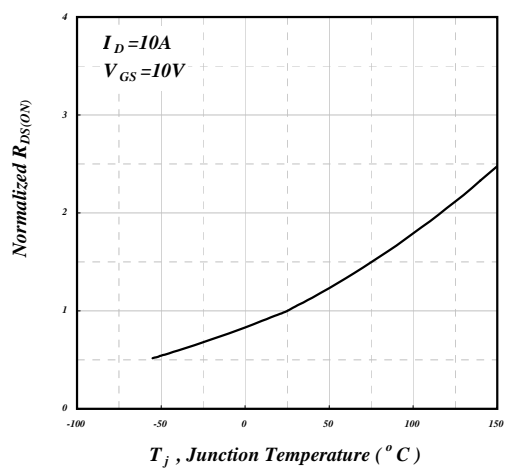


Fig 4. Normalized On-Resistance v.s. Junction Temperature

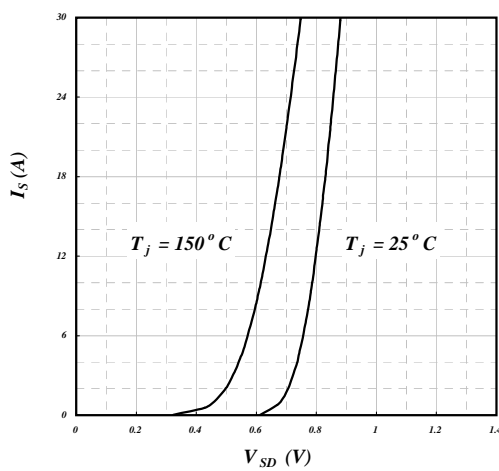


Fig 5. Forward Characteristic of Reverse Diode

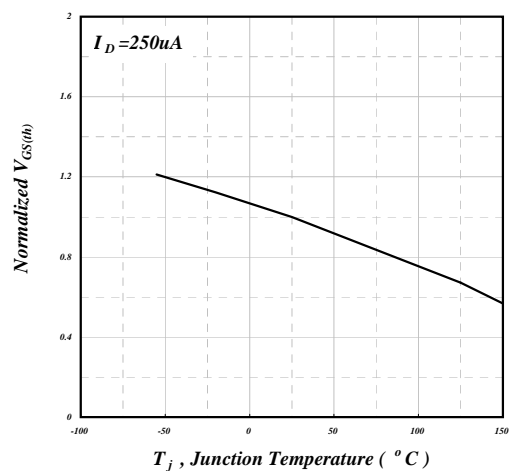


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

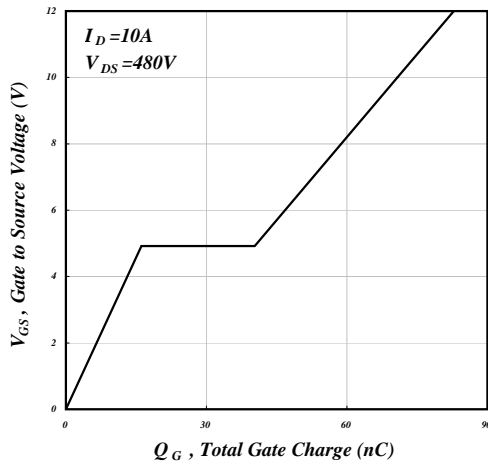


Fig 7. Gate Charge Characteristics

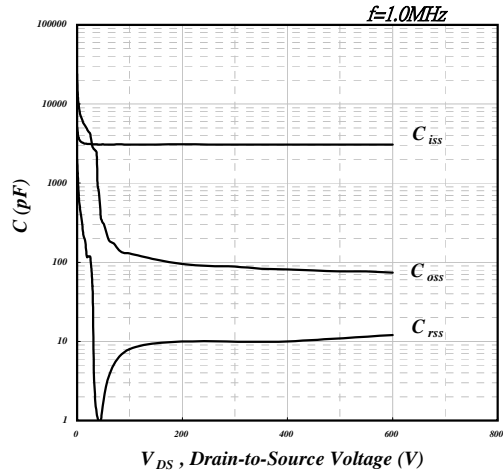


Fig 8. Typical Capacitance Characteristics

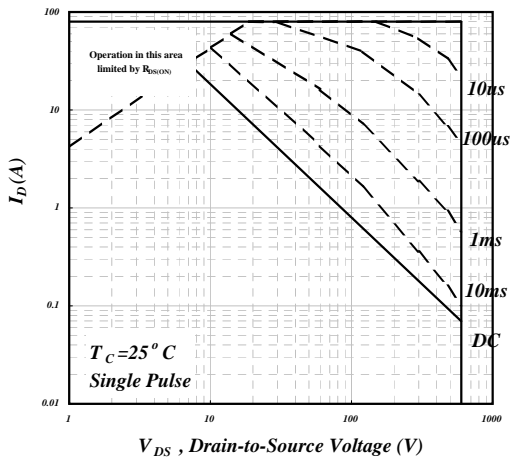


Fig 9. Maximum Safe Operating Area

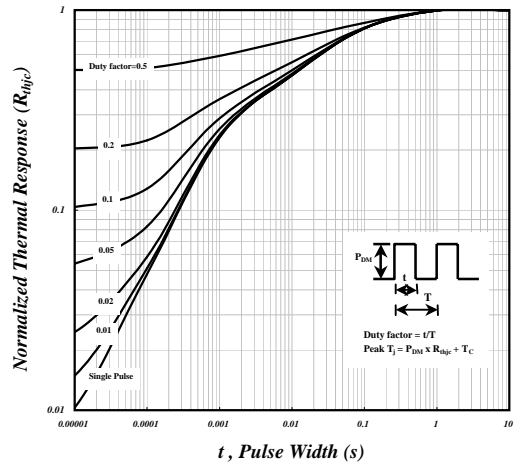


Fig 10. Effective Transient Thermal Impedance

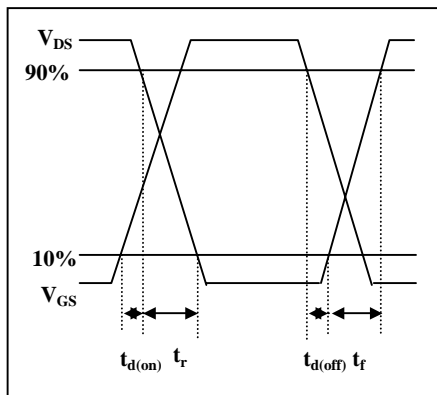


Fig 11. Switching Time Waveform

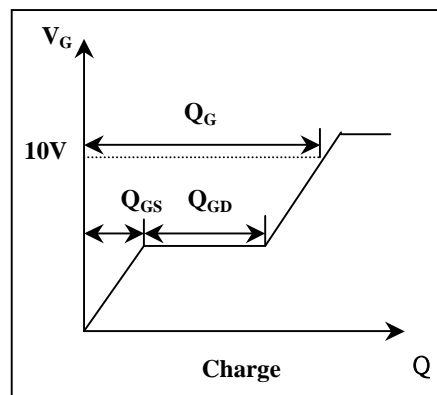


Fig 12. Gate Charge Waveform

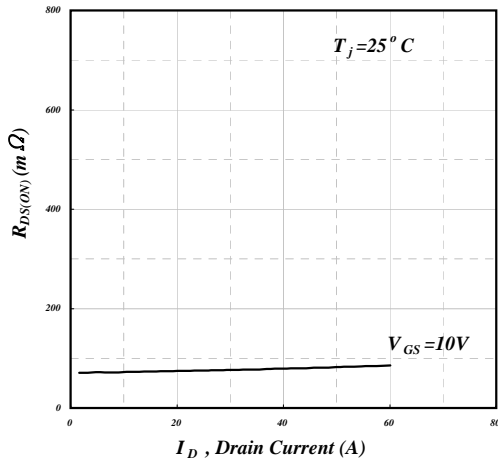


Fig 13. Typ. Drain-Source on State Resistance

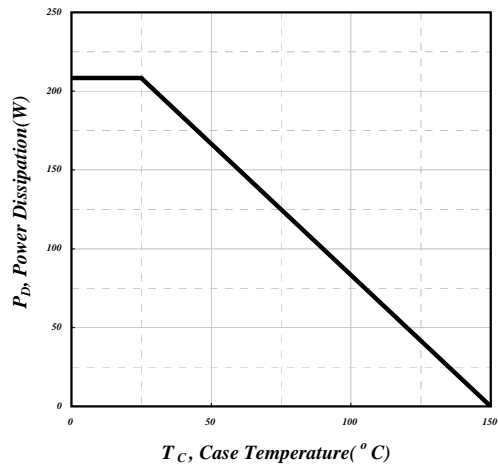


Fig 14. Total Power Dissipation

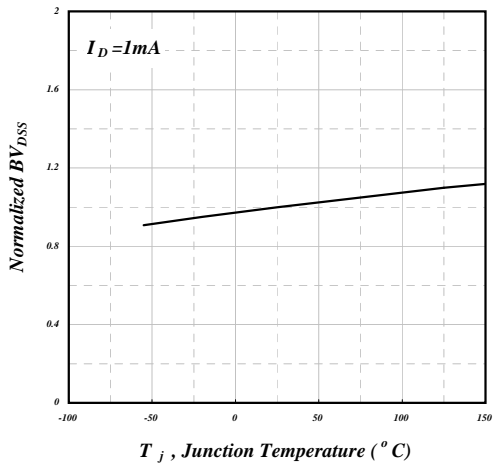
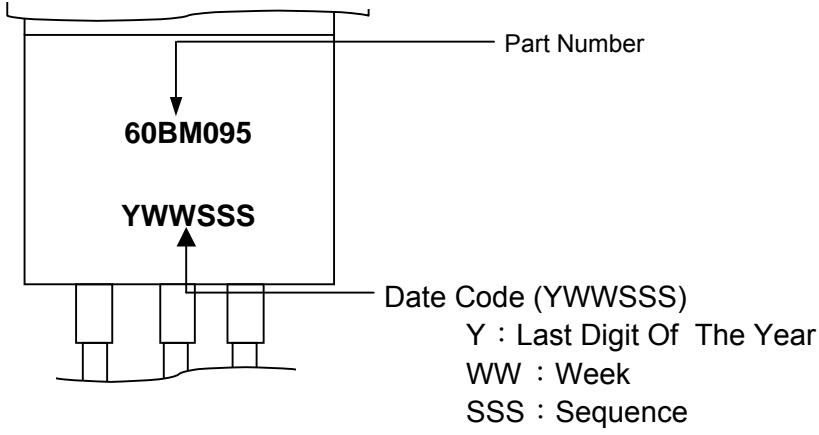
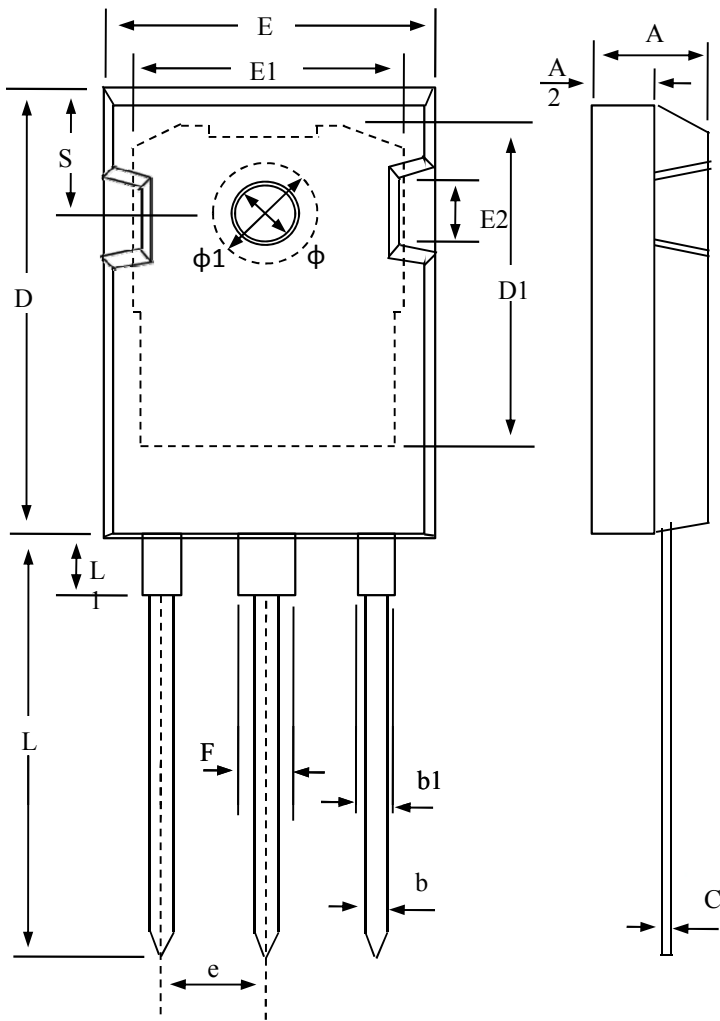


Fig 15. Normalized BV_{DSS} v.s. Junction Temperature

MARKING INFORMATION



Package Outline : TO-247



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.80	5.03	5.25
A2	1.90	2.05	2.20
E	15.75	15.95	16.15
E1	13.00	13.60	14.20
E2	3.60	4.35	5.10
D	20.80	20.95	21.10
D1	16.20	16.95	17.70
C	0.50	0.60	0.70
L	19.80	20.10	20.40
L1	4.10	4.25	4.40
F	2.80	3.10	3.40
b	1.05	1.20	1.35
b1	1.90	2.18	2.45
e	5.44 ref.		
ϕ	3.50	3.58	3.65
ϕ_1	7.18 ref.		
S	6.00	6.15	6.30

1. All Dimensions Are in Millimeters.
2. Dimension Does Not Include Mold Protrusions.

TO-247 FOOTPRINT :

